

# APPLICATION DATA SHEET

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Title of Invention: METHOD OF FABRICATING SEMICONDUCTOR DEVICE HAVING  
GROUP III NITRIDE

Legal Representative:

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Continuity Data:

This application is a reexamination of 09/389,024 A1 1999-09-02 6,117,700 A1 2000-09-12

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10-254996	JP	1998-09-09	Priority Claimed
10-326352	JP	1998-11-17	Priority Claimed

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